- **State-of-the-Art Advanced BiCMOS Technology (ABT) *Widebus*™ Design for 2.5-V and 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 2.3-V to 3.6-V V_{CC})**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **High Drive (–24/24 mA at 2.5-V V_{CC} and –32/64 mA at 3.3-V V_{CC})**
- **I_{off} and Power-Up 3-State Support Hot Insertion**
- **Use Bus Hold on Data Inputs in Place of External Pullup/Pulldown Resistors to Prevent the Bus From Floating**
- **Auto3-State Eliminates Bus Current Loading When Output Exceeds V_{CC} + 0.5 V**
- **Flow-Through Architecture Facilitates Printed Circuit Board Layout**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **ESD Protection Exceeds JESD-22**
  - **2000-V Human-Body Model**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101) (A114-A)**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **Packaged in Plastic Fine-Pitch Ball Grid Array Package**

NOTE: For tape and reel order entry:
The GKER package is abbreviated to KR.

description

The ’ALVTH32374 devices are 32-bit edge-triggered D-type flip-flops with 3-state outputs designed for 2.5-V or 3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as four 8-bit flip-flops, two 16-bit flip-flops, or one 32-bit flip-flop. On the positive transition of the clock (CLK), the Q outputs of the flip-flops take on the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

When V_{CC} is between 0 and 1.2 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.2 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

These devices are fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

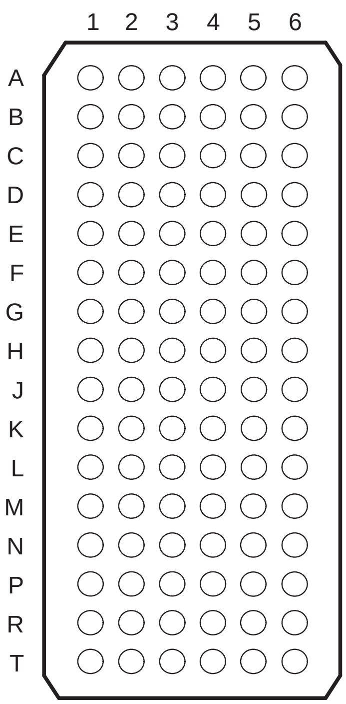
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54ALVTH32374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ALVTH32374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT Q
$\overline{OE}$	CLK	D	
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

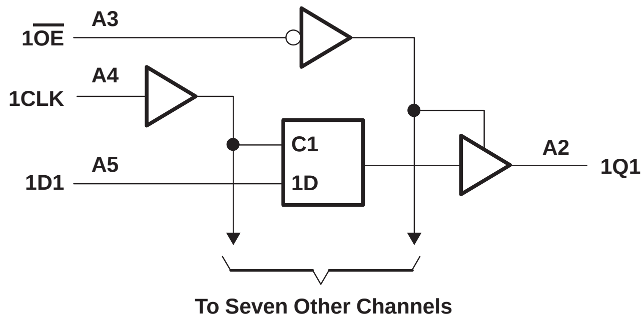
GKE PACKAGE
(TOP VIEW)

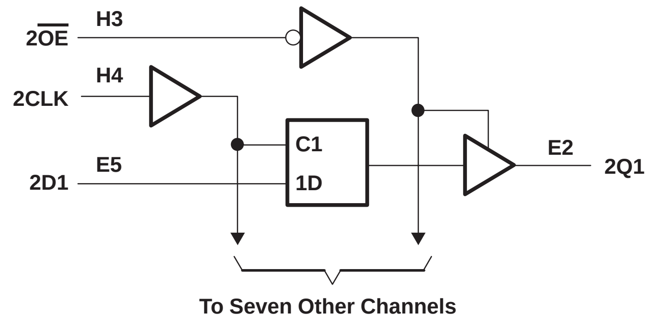


terminal assignments

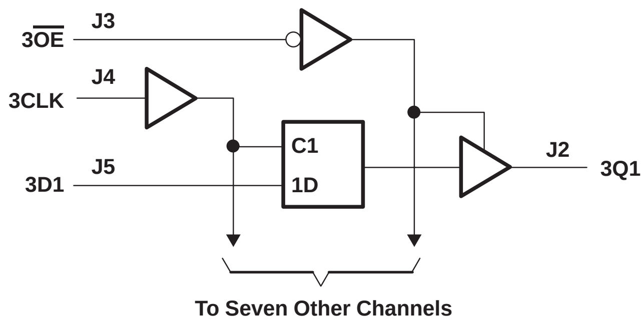
	1	2	3	4	5	6
A	1Q2	1Q1	1$\overline{OE}$	1CLK	1D1	1D2
B	1Q4	1Q3	GND	GND	1D3	1D4
C	1Q6	1Q5	$1V_{CC}$	$1V_{CC}$	1D5	1D6
D	1Q8	1Q7	GND	GND	1D7	1D8
E	2Q2	2Q1	GND	GND	2D1	2D2
F	2Q4	2Q3	$1V_{CC}$	$1V_{CC}$	2D3	2D4
G	2Q6	2Q5	GND	GND	2D5	2D6
H	2Q7	2Q8	2$\overline{OE}$	2CLK	2D8	2D7
J	3Q2	3Q1	3$\overline{OE}$	3CLK	3D1	3D2
K	3Q4	3Q3	GND	GND	3D3	3D4
L	3Q6	3Q5	$2V_{CC}$	$2V_{CC}$	3D5	3D6
M	3Q8	3Q7	GND	GND	3D7	3D8
N	4Q2	4Q1	GND	GND	4D1	4D2
P	4Q4	4Q3	$2V_{CC}$	$2V_{CC}$	4D3	4D4
R	4Q6	4Q5	GND	GND	4D5	4D6
T	4Q7	4Q8	4$\overline{OE}$	4CLK	4D8	4D7

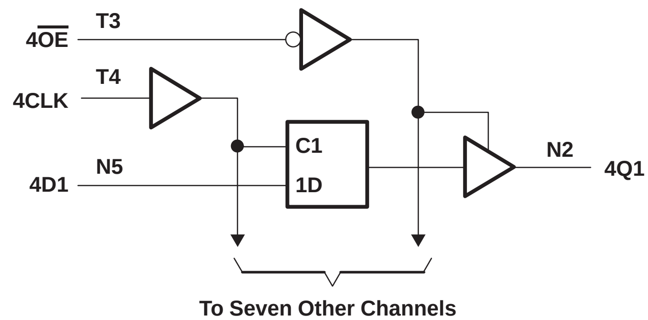
logic diagram (positive logic)





NOTE A: $1V_{CC}$ is associated with these channels.





NOTE B: $2V_{CC}$ is associated with these channels.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high state, V_O (see Note 1)	–0.5 V to 7 V
Output current in the low state, I_O: SN54ALVTH32374	96 mA
SN74ALVTH32374	128 mA
Output current in the high state, I_O: SN54ALVTH32374	–48 mA
SN74ALVTH32374	–64 mA
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I_{OK} ($V_O < 0$)	–50 mA
Package thermal impedance, θ_{JA} (see Note 2)	40°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions, V_{CC} = 2.5 V ± 0.2 V (see Note 3)

			SN54ALVTH32374			SN74ALVTH32374			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		2.3		2.7	2.3		2.7	V
V_{IH}	High-level input voltage		1.7			1.7			V
V_{IL}	Low-level input voltage				0.7			0.7	V
V_I	Input voltage		0	V_{CC}	5.5	0	V_{CC}	5.5	V
I_{OH}	High-level output current				–6			–8	mA
I_{OL}	Low-level output current				6			8	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				18			24	
Δt/Δv	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
Δt/ΔV_{CC}	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

recommended operating conditions, V_{CC} = 3.3 V ± 0.3 V (see Note 3)

			SN54ALVTH32374			SN74ALVTH32374			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		3		3.6	3		3.6	V
V_{IH}	High-level input voltage		2			2			V
V_{IL}	Low-level input voltage				0.8			0.8	V
V_I	Input voltage		0	V_{CC}	5.5	0	V_{CC}	5.5	V
I_{OH}	High-level output current				–24			–32	mA
I_{OL}	Low-level output current				24			32	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				48			64	
Δt/Δv	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
Δt/ΔV_{CC}	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH32374			SN74ALVTH32374			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.3 V to 2.7 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.3 V	I_{OH} = –6 mA	1.8						
			I_{OH} = –8 mA				1.8			
V_{OL}		V_{CC} = 2.3 V to 2.7 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 2.3 V	I_{OL} = 6 mA			0.4				
			I_{OL} = 8 mA						0.4	
			I_{OL} = 18 mA			0.5				
			I_{OL} = 24 mA						0.5	
I_I	Control inputs	V_{CC} = 2.7 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 2.7 V,	V_I = 5.5 V			10			10	
	Data inputs	V_{CC} = 2.7 V	V_I = 5.5 V			10			10	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}‡		V_{CC} = 2.3 V,	V_I = 0.7 V		115			115		µA
I_{BHH}§		V_{CC} = 2.3 V,	V_I = 1.7 V		–10			–10		µA
I_{BHLO}¶		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	300			300			µA
I_{BHHO}#		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	–300			–300			µA
I_{EX}‖		V_{CC} = 2.3 V,	V_O = 5.5 V			125			125	µA
$I_{OZ(PU/PD)}$☆		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZH}		V_{CC} = 2.7 V	V_O = 2.3 V, V_I = 0.7 V or 1.7 V			5			5	µA
I_{OZL}		V_{CC} = 2.7 V	V_O = 0.5 V, V_I = 0.7 V or 1.7 V			–5			–5	µA
I_{CC}		V_{CC} = 2.7 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.04	0.1		0.04	0.1	mA
			Outputs low		2.3	4.5		2.3	4.5	
			Outputs disabled		0.04	0.1		0.04	0.1	
C_i		V_{CC} = 2.5 V,	V_I = 2.5 V or 0		3.5			3.5		pF
C_o		V_{CC} = 2.5 V,	V_O = 2.5 V or 0		6			6		pF

† All typical values are at V_{CC} = 2.5 V, T_A = 25°C.
‡ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
§ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
¶ An external driver must source at least I_{BHLO} to switch this node from low to high.
# An external driver must sink at least I_{BHHO} to switch this node from high to low.
‖ Current into an output in the high state when V_O > V_{CC}
☆ High-impedance state during power up or power down

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH32374			SN74ALVTH32374			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 3 V to 3.6 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 3 V	I_{OL} = 16 mA						0.4	
			I_{OL} = 24 mA			0.5				
			I_{OL} = 32 mA						0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	Data inputs	V_{CC} = 3.6 V	V_I = 5.5 V			10			10	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}‡		V_{CC} = 3 V,	V_I = 0.8 V	75			75			µA
I_{BHH}§		V_{CC} = 3 V,	V_I = 2 V	–75			–75			µA
I_{BHLO}¶		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	500			500			µA
I_{BHHO}#		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	–500			–500			µA
I_{EX}‖		V_{CC} = 3 V,	V_O = 5.5 V			125			125	µA
$I_{OZ(PU/PD)}$☆		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZH}		V_{CC} = 3.6 V	V_O = 3 V, V_I = 0.8 V or 2 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V	V_O = 0.5 V, V_I = 0.8 V or 2 V			–5			–5	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.07	0.1		0.07	0.1	mA
			Outputs low		3.2	5		3.2	5	
			Outputs disabled		0.07	0.1		0.07	0.1	
ΔI_{CC}□		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.4			0.4	mA
C_i		V_{CC} = 3.3 V,	V_I = 3.3 V or 0		3.5			3.5		pF
C_o		V_{CC} = 3.3 V,	V_O = 3.3 V or 0		6			6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
§ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
¶ An external driver must source at least I_{BHLO} to switch this node from low to high.
# An external driver must sink at least I_{BHHO} to switch this node from high to low.
‖ Current into an output in the high state when V_O > V_{CC}
☆ High-impedance state during power up or power down
□ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

			SN54ALVTH32374		SN74ALVTH32374		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			150		150	MHz
t_w	Pulse duration, CLK high or low		1.5		1.5		ns
t_{su}	Setup time, data before CLK↑	Data high	1.1		1		ns
		Data low	1.4		1.3		
t_h	Hold time, data after CLK↑	Data high	0.6		0.5		ns
		Data low	0.9		0.8		

timing requirements over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

			SN54ALVTH32374		SN74ALVTH32374		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			250		250	MHz
t_w	Pulse duration, CLK high or low		1.5		1.5		ns
t_{su}	Setup time, data before CLK↑	Data high	1.1		1		ns
		Data low	1.6		1.5		
t_h	Hold time, data after CLK↑	Data high	0.6		0.5		ns
		Data low	1.1		1		

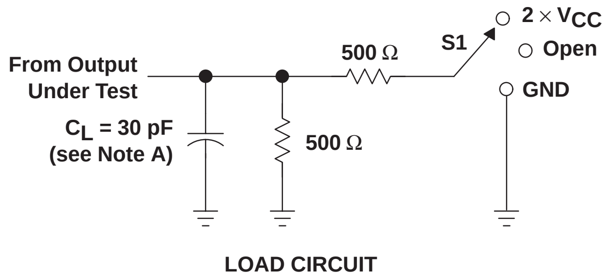
switching characteristics over recommended operating free-air temperature range, C_L = 30 pF, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH32374		SN74ALVTH32374		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			150		150		MHz
t_{PLH}	CLK	Q	1.4	3.9	1.5	3.8	ns
t_{PHL}			1.4	3.9	1.5	3.8	
t_{PZH}	$\overline{OE}$	Q	1	4.2	1	4.1	ns
t_{PZL}			1	3.8	1	3.7	
t_{PHZ}	$\overline{OE}$	Q	1.7	4.3	1.8	4.2	ns
t_{PLZ}			1	3.5	1	3.4	

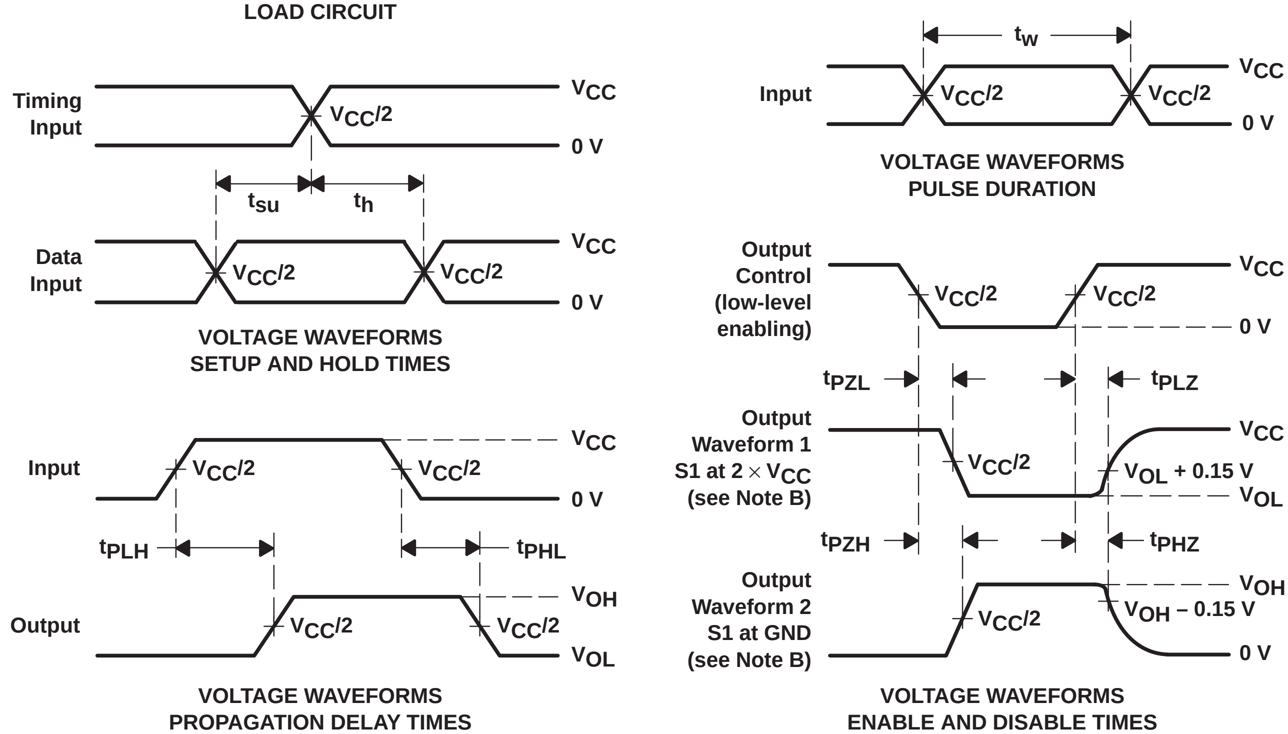
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH32374		SN74ALVTH32374		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			250		250		MHz
t_{PLH}	CLK	Q	1	3.4	1	3.2	ns
t_{PHL}			1	3.3	1	3.2	
t_{PZH}	$\overline{OE}$	Q	1	3.9	1	3.8	ns
t_{PZL}			1	3.4	1	3.3	
t_{PHZ}	$\overline{OE}$	Q	1	4.7	1	4.6	ns
t_{PLZ}			1	4.4	1	4.2	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V



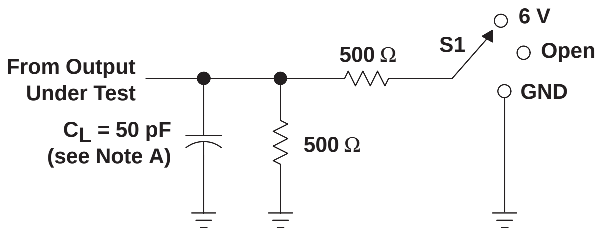
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.

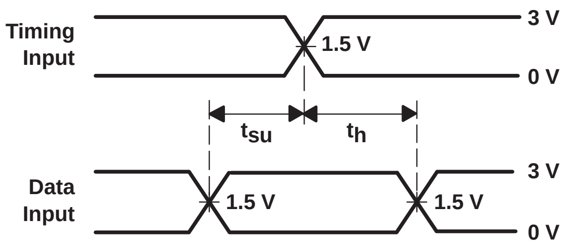
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 3.3 V ± 0.3 V

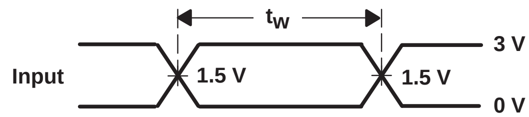


LOAD CIRCUIT

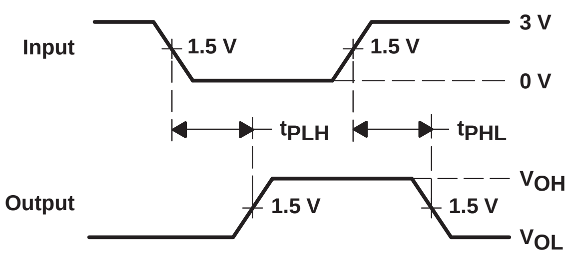
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



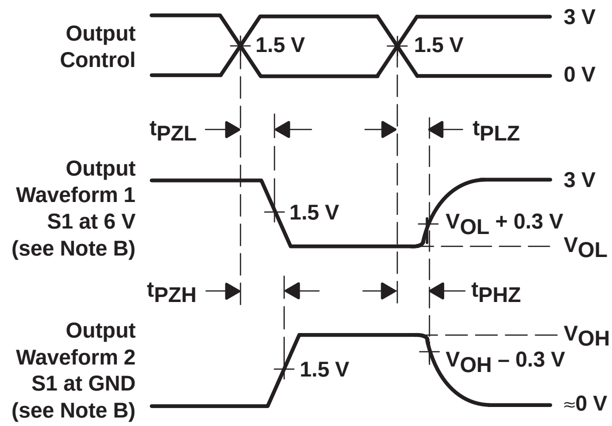
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
74ALVTH32374ZKER	ACTIVE	LFBGA	ZKE	96	1000	Green (RoHS & no Sb/Br)	SNAGCU	Level-3-260C-168 HR	-40 to 85	VL374	Samples
SN74ALVTH32374KR	NRND	LFBGA	GKE	96	1000	TBD	SNPB	Level-2-235C-1 YEAR	-40 to 85	VL374	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

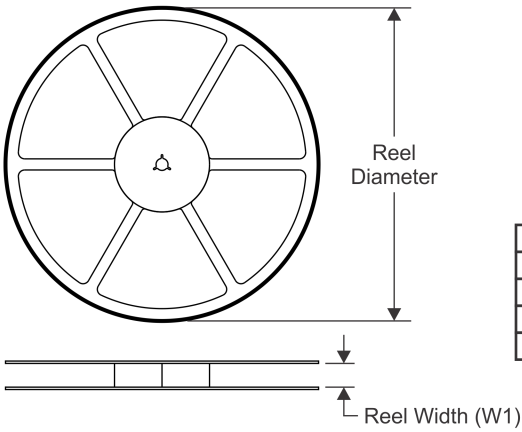
(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

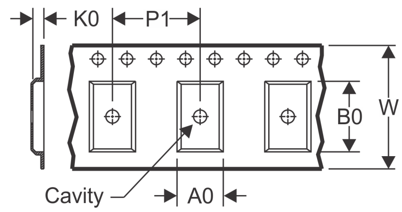
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

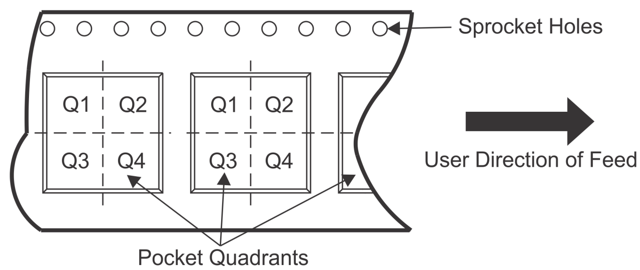


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

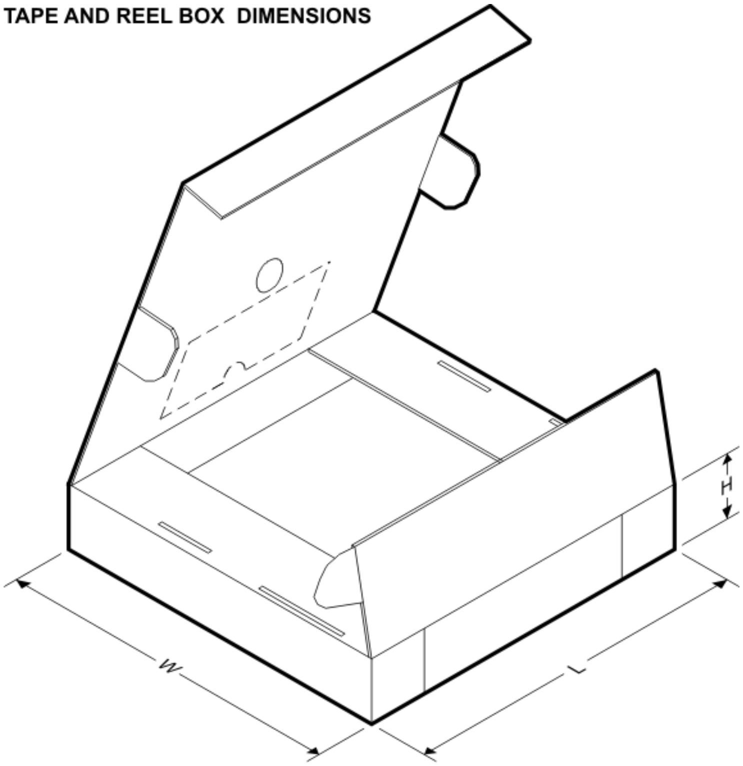
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74ALVTH32374ZKER	LFBGA	ZKE	96	1000	330.0	24.4	5.7	13.7	2.0	8.0	24.0	Q1
SN74ALVTH32374KR	LFBGA	GKE	96	1000	330.0	24.4	5.7	13.7	2.0	8.0	24.0	Q1

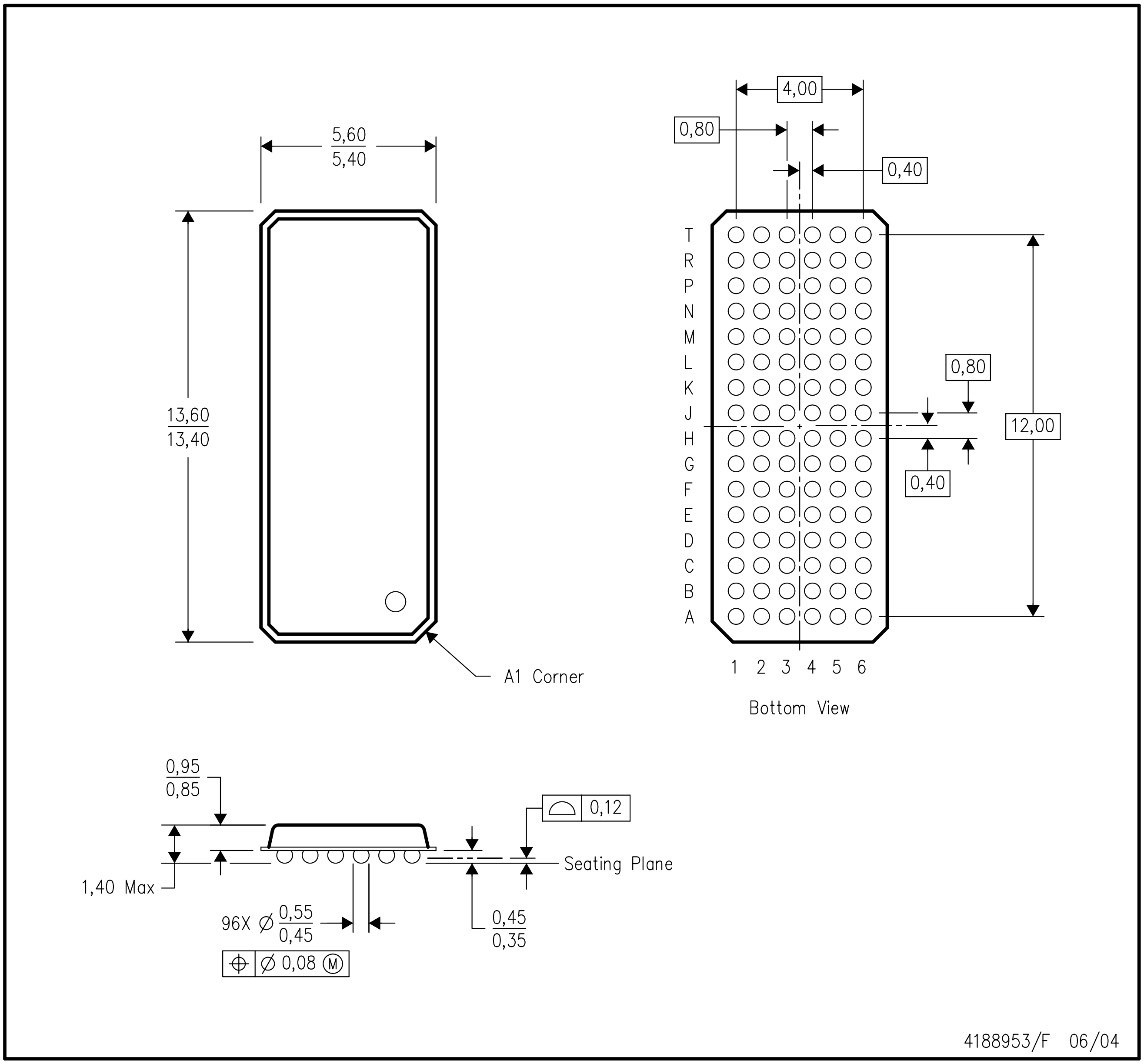
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

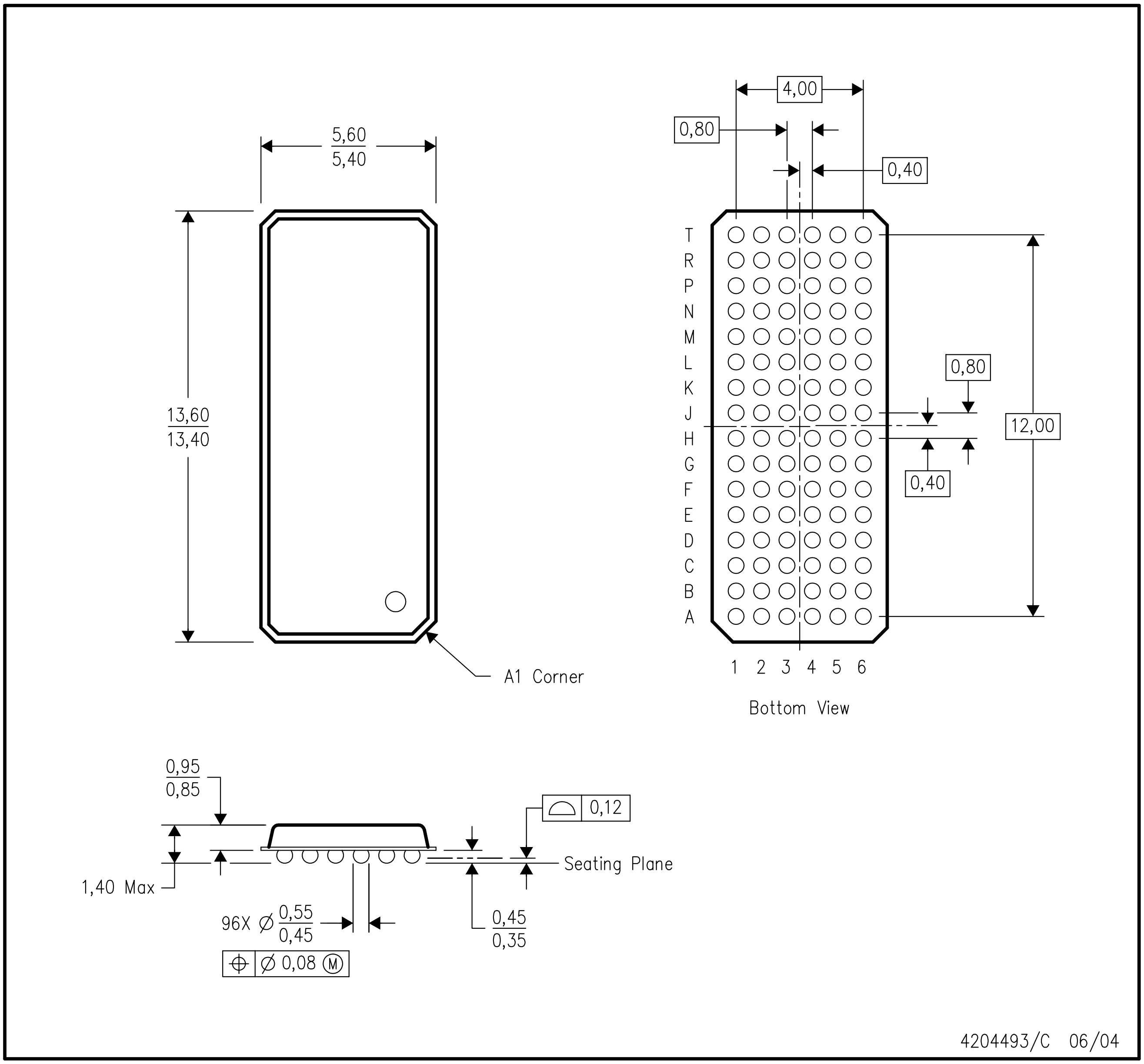
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74ALVTH32374ZKER	LFBGA	ZKE	96	1000	336.6	336.6	41.3
SN74ALVTH32374KR	LFBGA	GKE	96	1000	336.6	336.6	41.3

GKE (R–PBGA–N96) PLASTIC BALL GRID ARRAY



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MO–205 variation CC.
- D. This package is tin–lead (SnPb). Refer to the 96 ZKE package (drawing 4204493) for lead–free.

ZKE (R–PBGA–N96) PLASTIC BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Falls within JEDEC MO–205 variation CC.
D. This package is lead–free. Refer to the 96 GKE package (drawing 4188953) for tin–lead (SnPb).